

INCHANGE SEMICONDUCTOR

Isc N-Channel MOSFET Transistor

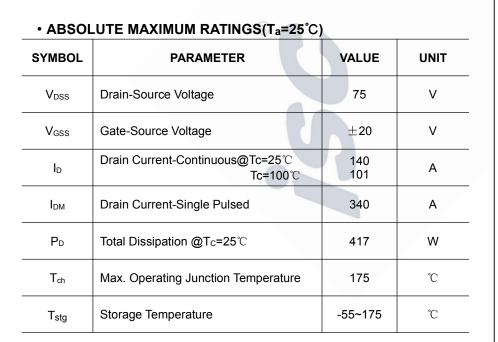
AOT472

• FEATURES

- With To-220 package
- · Low input capacitance and gate charge
- · Low gate input resistance
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

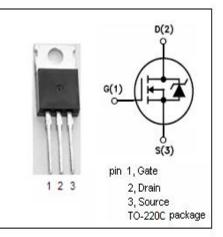
Switching applications

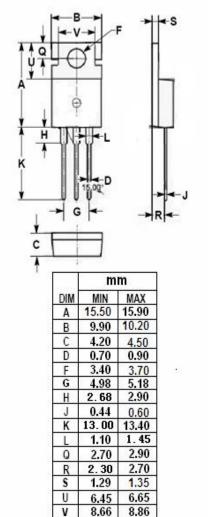


THERMAL CHARACTERISTICS

SYMBOL	PARAMETER		UNIT	
Rth(ch-c)	Channel-to-case thermal resistance	0.36	°C /W	
Rth(ch-a)	Channel-to-ambient thermal resistance	65	°C/W	

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UTT50N06L-TA3

ELECTRICAL CHARACTERISTICS

 $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D = 0.25mA	75			V
V _{GS} (th)	Gate Threshold Voltage	V _{DS} =V _{GS} ; I _D =0.25mA	1.0		3.0	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D =30A		7.4	8.9	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V;V _{DS} = 0V			±0.1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =75V; V _{GS} = 0V			1	μ Α
V _{SDF}	Diode forward voltage	I _{SD} =1A, V _{GS} = 0V			1	v

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